

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P. D. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING I	DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/656,312 09/05/2003		2003	Sylvia H. Pas	TI-22398.1	8214	
23494	7590	04/28/2004		EXAMINER		
	STRUMENTS	AHMED,	AHMED, SHAMIM			
P O BOX 65 DALLAS, 7	5474, M/S 399 TX - 75265	9		ART UNIT	PAPER NUMBER	
,				1765		
				DATE MAILED: 04/28/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.		Applicant(s)	•			
		10/656,312		PAS, SYLVIA H.				
	Office Action Summary	Examiner		Art Unit	-			
		Shamim Ahmed		1765				
Period fo	The MAILING DATE of this communication or Reply	appears on the cove	r sheet with the co	orrespondence addre	:SS			
A SH THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR RE MAILING DATE OF THIS COMMUNICATIO nsions of time may be available under the provisions of 37 CFF SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a period for reply is specified above, the maximum statutory per re to reply within the set or extended period for reply will, by state the reply received by the Office later than three months after the med patent term adjustment. See 37 CFR 1.704(b).	N. R 1.136(a). In no event, how reply within the statutory mir riod will apply and will expire atute, cause the application t	ever, may a reply be tim nimum of thirty (30) days SIX (6) MONTHS from to become ABANDONED	ely filed s will be considered timely. the mailing date of this comm O (35 U.S.C. § 133).	unication.			
Status								
1)[\inf	Responsive to communication(s) filed on 05	5 September 2003.						
		his action is non-fin	al.					
3)	Since this application is in condition for allo	wance except for fo	rmal matters, pro	secution as to the m	erits is			
	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposit	ion of Claims							
5)[Claim(s) <u>14-20</u> is/are pending in the applicated 4a) Of the above claim(s) is/are with Claim(s) is/are allowed. Claim(s) <u>14-20</u> is/are rejected. Claim(s) is/are objected to.		ation.					
′=	Claim(s) are subject to restriction an	d/or election require	ment.					
Applicat	ion Papers							
10)⊠	The specification is objected to by the Examine The drawing(s) filed on <u>05 September 2003</u> Applicant may not request that any objection to Replacement drawing sheet(s) including the cor The oath or declaration is objected to by the	is/are: a)⊠ accept the drawing(s) be held rection is required if th	l in abeyance. See ne drawing(s) is obj	37 CFR 1.85(a). ected to. See 37 CFR	1.121(d).			
Priority ι	ınder 35 U.S.C. § 119							
a)	Acknowledgment is made of a claim for fore All b) Some * c) None of: 1. Certified copies of the priority docum 2. Certified copies of the priority docum 3. Copies of the certified copies of the papplication from the International Bur See the attached detailed Office action for a	ents have been rece ents have been rece priority documents he reau (PCT Rule 17.2	eived. eived in Application ave been receivee 2(a)).	on No d in this National Sta	age			
Attachmen								
2) Notice (3) Information	te of References Cited (PTO-892) te of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB, or No(s)/Mail Date	/08) 5) 🔲	Interview Summary (Paper No(s)/Mail Da Notice of Informal Pa Other:		i2)			

Application/Control Number: 10/656,312

Art Unit: 1765

DETAILED ACTION

Claim Objections

1. Claim 15 is objected to because of the following informalities: in claim 15, line 3, the use of "a" is unnecessary between the phrase "the " and "transfer chamber".

Appropriate correction is required.

Claim Rejections - 35 USC § 112

- 2. The following is a quotation of the second paragraph of 35 U.S.C. 112:
 - The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 3. Claims 14-20 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- 4. Claim 14 recites the limitation "the oxide *layer*" in line 6. There is insufficient antecedent basis for this limitation in the claim.
- 5. Regarding claim 17, the phrase "solution comprises .049% to 49% HF" renders the claim(s) indefinite because it is unclear whether the percent (%) HF solution is by weight or by volume.

Claim Rejections - 35 USC § 102

6. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

⁽b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Application/Control Number: 10/656,312

Art Unit: 1765

7. Claims 14-19 are rejected under 35 U.S.C. 102(b) as being anticipated by Kikuchi (5,620,559).

Kikuchi discloses a process of removing oxide layer by exposing a semiconductor wafer comprises silicon substrate (104) in a HF processing chamber (105), wherein the HF is 10 % by volume (col.9, lines 32-62, figure 10).

Kikuchi also discloses that the silicon wafer is then align or line up for automatically transferring to a process module such as a deposition chamber (140) (col.11, lines 28-42 and figures 10 and 11).

8. Claims 14-16,18-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Hawthorne et al (5,770,263).

Hawthorne et al disclose a process of removing oxide film from a silicon wafer surface including the process steps of exposing a silicon wafer to a vaporous solution of hydrofluoric acid (HF) for removing the oxide film, wherein the process is performed in a cluster tool is generally defined as a transfer module which transfer the wafer into a first chamber such as HF vapor clean and then the wafer is transfer to a second chamber such as a deposition chamber, in which at least one metallic film is intentionally deposited (col.4, lines 12-30).

As to claim 20, Hawthorne et al teach that the deposited film comprises polysilicon and tungsten (col.4, lines 12-13).

9. Claims 14-16,18-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Huanga et al (5,670,431).

Application/Control Number: 10/656,312

Art Unit: 1765

Huanga et al disclose a process of deposition of a thin layer of silicon nitride on a semiconductor wafer substrate, wherein the substrate is subjected to a HF vapor cleaning process prior to the deposition process (col.5, lines 38-45).

Huanga et al also disclose that a wafer transfer system (52) transfer a single wafer from wafer loading station (58) to the HF cleaning system (56) and than to the film forming chamber (54) (col.6, line 65-col.7, line 15 and Figure 6).

Conclusion

10. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Saga et al (5,679,171) disclose a cleaning process for oxide film using HF vapor.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (571) 272-1457. The examiner can normally be reached on M-Thu (7:00-5:30) Every Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 1765

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Shamim Ahmed Examiner Art Unit 1765

SA April 22, 2004